

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled)

2. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate;

a data line driver circuit over the substrate; and

a dividing circuit over the substrate, for dividing a signal into n signals, and inputting the n signals to n pixels among the plurality of pixels through n video input signal lines,

~~wherein the dividing circuit divides a signal into n signals, and~~

wherein the n signals are inputted into ~~corresponding~~ the n pixels by a timing signal supplied from the data driver circuit, simultaneously.

3. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate, for dividing a signal into n signals, and inputting the n signals to n pixels among the plurality of pixels through n video input signal lines,

~~wherein the dividing circuit divides a signal into n signals, and~~

wherein the n signals are inputted into ~~corresponding~~ the n pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

4. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate;

a data line driver circuit over the substrate;

a dividing circuit over the substrate ~~[[;]],~~ for dividing three signals corresponding to colors R, G and B into 3n signals, and inputting the 3n signals to 3n pixels among the plurality of pixels through 3n video input signal lines,

~~wherein the dividing circuit divides three signals corresponding to colors R, G and B into 3n signals,~~

wherein the 3n signals are inputted into ~~corresponding~~ the 3n pixels by a timing signal supplied from the data driver circuit, simultaneously.

5. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into 3n signals into 3n signals, and inputting the 3n signals to 3n pixels among the plurality of pixels through 3n video input signal lines,

~~wherein the dividing circuit divides three signals corresponding to colors R, G and B into 3n signals, and~~

wherein the 3n signals are inputted into ~~corresponding~~ the 3n pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

6. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit over the substrate; and

a dividing circuit over the substrate, for dividing a signal into n signals, and inputting the n signals to n thin film transistors corresponding to n pixels among the plurality of pixels through n video input signal lines,

~~wherein the dividing circuit divides a signal into n signals, and~~

wherein the n signals are inputted into the n thin film transistors corresponding to n pixels by a timing signal supplied from the data driver circuit, simultaneously.

7. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate, for dividing a signal into n signals, and inputting the n signals to n thin film transistors corresponding to n pixels among the plurality of pixels through n video input signal lines,

~~wherein the dividing circuit divides a signal into n signals, and~~

wherein the n signals are inputted into the n thin film transistors corresponding to n pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

8. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit over the substrate;

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into 3n signals, and inputting the 3n signals to 3n thin film transistors corresponding to 3n pixels among the plurality of pixels through 3n video input signal lines.[:]]

~~wherein the dividing circuit divides three signals corresponding to colors R, G and B into 3n signals,~~

wherein the 3n signals are inputted into the 3n thin film transistors corresponding to 3n pixels by a timing signal supplied from the data driver circuit, simultaneously.

9. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into 3n signals, and inputting the 3n signals to 3n thin film transistors corresponding to 3n pixels among the plurality of pixels through 3n video input signal lines,

~~wherein the dividing circuit divides three signals corresponding to colors R, G and B into 3n signals, and~~

wherein the 3n signals are inputted into the 3n thin film transistors corresponding to 3n pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

10. (Previously Presented) A semiconductor device according to claim 2, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

11. (Previously Presented) A semiconductor device according to claim 3, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

12. (Previously Presented) A semiconductor device according to claim 4, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

13. (Previously Presented) A semiconductor device according to claim 5, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

14. (Previously Presented) A semiconductor device according to claim 6, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

15. (Previously Presented) A semiconductor device according to claim 7, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

16. (Previously Presented) A semiconductor device according to claim 8, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

17. (Previously Presented) A semiconductor device according to claim 9, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

18. (Previously Presented) A semiconductor device according to claim 2, wherein the substrate comprises glass.

19. (Previously Presented) A semiconductor device according to claim 3, wherein the substrate comprises glass.

20. (Previously Presented) A semiconductor device according to claim 4, wherein the substrate comprises glass.

21. (Previously Presented) A semiconductor device according to claim 5, wherein the substrate comprises glass.

22. (Previously Presented) A semiconductor device according to claim 6, wherein the substrate comprises glass.

23. (Previously Presented) A semiconductor device according to claim 7, wherein the substrate comprises glass.

24. (Previously Presented) A semiconductor device according to claim 8, wherein the substrate comprises glass.

25. (Previously Presented) A semiconductor device according to claim 9, wherein the substrate comprises glass.

26. (Previously Presented) A semiconductor device according to claim 6, wherein the thin film transistor comprises polycrystalline silicon film.

27. (Previously Presented) A semiconductor device according to claim 7, wherein the thin film transistor comprises polycrystalline silicon film.

28. (Previously Presented) A semiconductor device according to claim 8, wherein the thin film transistor comprises polycrystalline silicon film.

29. (Previously Presented) A semiconductor device according to claim 9, wherein the thin film transistor comprises polycrystalline silicon film.

30. (Previously Presented) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

31. (Previously Presented) A semiconductor device according to claim 3, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

32. (Previously Presented) A semiconductor device according to claim 4, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

33. (Previously Presented) A semiconductor device according to claim 5, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle

type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

34. (Previously Presented) A semiconductor device according to claim 6, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

35. (Previously Presented) A semiconductor device according to claim 7, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

36. (Previously Presented) A semiconductor device according to claim 8, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

37. (Previously Presented) A semiconductor device according to claim 9, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.